



PT9701B

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI PT9701B** is a Common Emitter Device Designed for Class A, AB and C Amplifier Applications in the 225 - 400 MHz Military Communications Band.

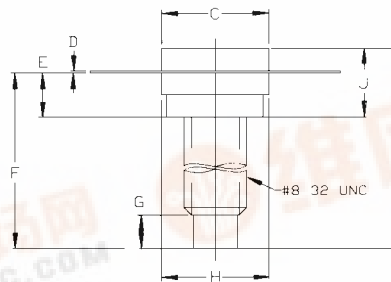
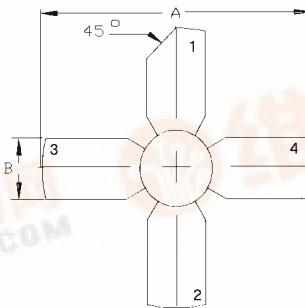
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- High Gain

MAXIMUM RATINGS

I_C	1.25 A
V_{CES}	45 V
P_{DISS}	14 W @ $T_C = 25^\circ\text{C}$
T_J	-55°C to $+200^\circ\text{C}$
T_{STG}	-55°C to $+200^\circ\text{C}$
q_{JC}	12°C/W

PACKAGE STYLE .280 4L STUD



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25.65	1.055/26.80
B	.220/5.59	.230/5.84
C	.270/6.86	.285/7.24
D	.003/0.08	.007/0.18
E	.117/2.97	.137/3.48
F	.5/2/14.53	
G	.130/3.30	
H	.275/6.99	.285/7.24
I	.640/16.26	
J	.175/4.45	.21/75.51

1 = COLLECTOR 2 = BASE
3 & 4 = EMITTER

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 20\text{ mA}$	25			V
BV_{CES}	$I_C = 10\text{ mA}$	45			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	3.5			V
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 200\text{ mA}$	15			---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			7.0	pF
P_G h_c	$V_{CE} = 28\text{ V}$ $P_{out} = 5.0\text{ W}$ $f = 400\text{ MHz}$	10 50	12 55		dB %

